PURE STRIP

STABILIZED SULFURIC ACID-HYDROGEN PEROXIDE COMPOUND

DESCRIPTION:

Pure Strip is suitable for stripping both positive and negative photoresists in addition to other organic compounds in a variety of semiconductor, photomask, and IC photolithography compounds. High yields can be achieved due to the high purity/low particulate composition of Pure Strip.

Advantages Pure Strip include negligible attack on exposed metal surfaces, including aluminum, vs. other acidic formulations, residue-free rinsing, and extended bath life (minimum of five days at room temperature). Pure Strip is ready to use and requires no mixing.

TYPICAL ASSAY:

HYDROGEN PEROXIDE ASSAY	< 1%
PEROXYMONOSULFURIC ACID ASSAY	4.0-5.15%
SULFURIC ACID ASSAY	89-91%

Aluminum (Al)	ppb	Max 1
Antimony (Sb)	ppb	Max 1
Arsenic (As)	ppb	Max 1
Barium (Ba)	ppb	Max 1
Beryllium (Be)	ppb	Max 1
Bismuth (Bi)	ppb	Max 1
Boron (B)	ppb	Max 1
Cadmium (Cd)	ppb	Max 1
Calcium (Ca)	ppb	Max 5
Chromium (Cr)	ppb	Max 1
Cobalt (Co)	ppb	Max 1
Copper (Cu)	ppb	Max 1
Gallium (Ga)	ppb	Max 1
Germanium (Ge)	ppb	Max 1
Iron (Fe)	ppb	Max 5
Lead (Pb)	ppb	Max 1
Lithium (Li)	ppb	Max 1
Magnesium (Mg)	ppb	Max 1
Manganese (Mn)	ppb	Max 1

Molybdenum (Mo)	ppb	Max 1
Nickel (Ni)	ppb	Max 1
Niobium (Nb)	ppb	Max 1
Potassium (K)	ppb	Max 1
Silver (Ag)	ppb	Max 1
Sodium (Na)	ppb	Max 1
Strontium (Sr)	ppb	Max 1
Tantalum (Ta)	ppb	Max 1
Thallium (Tl)	ppb	Max 1
Tin (Sn)	ppb	Max 1
Titanium (Ti)	ppb	Max 1
Vanadium (V)	ppb	Max 1
Zinc (Zn)	ppb	Max 5
Zirconium (Zr)	ppb	Max 1

APPLICATION:

Pure Strip may be used at room temperature or at elevated temperature. Higher temperatures will increase the activity but decrease the bath life (1 day at 60-80 ºC). Substrates are stripped of photoresist and cleaned effectively with minimal attack on aluminum (approximately 35 angstroms/minute at room temperature) and negligible attack on other metals and alloys such as titanium, ti-tungsten, copper, tantalum silicide, and ITO.

TRANSENE
COMPANY, INC.